January 1993 Revised August 2000

FAIRCHILD

SEMICONDUCTOR

SCAN182541A **Non-Inverting Line Driver** with 25 Ω Series Resistor Outputs

General Description

The SCAN182541A is a high performance BiCMOS line driver featuring separate data inputs organized into dual 9bit bytes with byte-oriented paired output enable control signals. This device is compliant with IEEE 1149.1 Standard Test Access Port and Boundary-Scan architecture with the incorporation of the defined Boundary-Scan test logic and test access port consisting of Test Data Input (TDI), Test Data Out (TDO), Test Mode Select (TMS), and Test Clock (TCK).

Features

- IEEE 1149.1 (JTAG) Compliant
- High performance BiCMOS technology
- \blacksquare 25 Ω series resistor outputs eliminate need for external terminating resistors
- Dual output enable signals per byte
- 3-STATE outputs for bus-oriented applications
- 25 mil pitch SSOP (Shrink Small Outline Package)
- Includes CLAMP, IDCODE and HIGHZ instructions
- Additional instructions SAMPLE-IN, SAMPLE-OUT and EXTEST-OUT

SCAN182541A Non-Inverting Line Driver with 25 Ω Series Resistor Outputs

- Power up 3-STATE for hot insert
- Member of Fairchild's SCAN Products

Ordering Code:

Order Number	Package Number	Package Description
SCAN182541ASSC	MS56A	56-Lead Shrink Small Outline Package (SSOP), JEDEC MO-118, 0.300 Wide
Devices also available in	Tape and Reel. Specify	by appending the suffix letter "X" to the ordering code.
Connection	Diagram	Pin Descriptions

Connection Diagram

TMS —		56 TDI
A0 ₀ —	2	55 — Al _o
AOE -	3	54 - AOE
A01-	4	53 — Al ₁
A02 -	5	52 Al2
GND —	6	5 I — GND
A03 —	7	50 — AI3
A04 -	8	49 AI4
v _{cc} —	9	48 — V _{CC}
A05 —	10	47 — Al ₅
A0 ₆ —	11	46 — Al ₆
GND —	12	45 — GND
A07 —	13	44 — Al ₇
A0 ₈ —	14	43 — Al ₈
во _о —	15	4 2 — Bl ₀
во ₁ —	16	41 — BI ₁
GND —	17	40 — GND
во ₂ —	18	39 — BI ₂
во3 —	19	38 — ві _з
v _{cc} —	20	37 — V _{CC}
во ₄ —	21	36 — BI ₄
во ₅ —	22	35 — ВІ ₅
GND —	23	34 — GND
во ₆ —	24	зз — ві ₆
во ₇ —	25	32 — ВІ ₇
BOE1	26	31 BOE
во ₈ —	27	30 — BI ₈
тво —	28	29 — ТСК

Pin Descriptions

Pin Names	Description
AI ₍₀₋₈₎	Input Pins, A Side
BI ₍₀₋₈₎	Input Pins, B Side
AOE ₁ , AOE ₂	3-STATE Output Enable Input Pins, A Side
BOE ₁ , BOE ₂	3-STATE Output Enable Input Pins, B Side
AO ₍₀₋₈₎	Output Pins, A Side
BO ₍₀₋₈₎	Output Pins, B Side

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В

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Truth Tables Inputs Inputs AO₍₀₋₈₎ BO₍₀₋₈₎ †AOE₂ †AOE₁ AI₍₀₋₈₎ †BOE₁ †BOE₂ BI₍₀₋₈₎ L L Н Н L L Н Н Ζ н Х Х н Х Х Ζ Х н Х Ζ Х н Х Ζ L Т L L L I. L L H = HIGH Voltage Level L = LOW Voltage Level Z = High Impedance † = Inactive-to-active transition must occur to enable outputs upon X = Immaterial power-up. **Block Diagrams** Byte A TYPE 1 BSR 41 AOE1 TYPE2 BSR 39 TYPE 1 BSR 40 AOE INSTRUCTION 3-STATE -NON-INVERTING BUFFER TYPE 1 TYPE2 BSR 27-35 BSR 9-17 AI[0-8] AO [0-8] Tap Controller TO BSR[41] FROM BSR [0] IDCODE REGISTER BYPASS REGISTER TDI INSTRUCTION REGISTER TDO INSTRUCTION 3-STATE TEST TMS ACCES PORT TCK (TAP) Byte B NON-INVERTING BUFFER TYPE 1 TYPE2 BSR 18-26 BSR 0-8 BI [0-8] •B0 [0-8] TYPE1 INSTRUCTION 3-STATE-BSR 38 BOE₁ TYPE2 BSR 36 TYPE1 BSR 37 BOE₂ Note: BSR stands for Boundary Scan Register.

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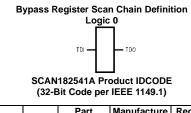
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Description of BOUNDARY-SCAN Circuitry

The scan cells used in the BOUNDARY-SCAN register are one of the following two types depending upon their location. Scan cell TYPE1 is intended to solely observe system data, while TYPE2 has the additional ability to control system data.

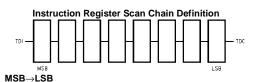
Scan cell TYPE1 is located on each system input pin while scan cell TYPE2 is located at each system output pin as well as at each of the two internal active-high output enable signals. AOE controls the activity of the A-outputs while BOE controls the activity of the B-outputs. Each will activate their respective outputs by loading a logic high.

The BYPASS register is a single bit shift register stage identical to scan cell TYPE1. It captures a fixed logic low.

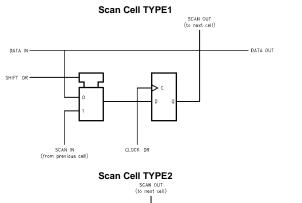


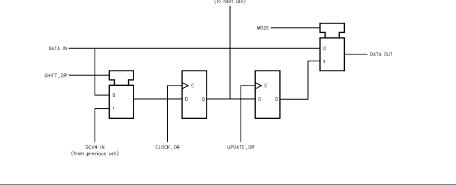
Version	Entity	Part	Manufacture r	Required b y
		Number	ID	1149.1
0000	111111	000000100 1	00000001111	1
MSB				LSB

The INSTRUCTION register is an 8-bit register which captures the default value of 10000001 (SAMPLE/PRELOAD) during the CAPTURE-IR instruction command. The benefit of capturing SAMPLE/PRELOAD as the default instruction during CAPTURE-IR is that the user is no longer required to shift in the 8-bit instruction for SAMPLE/PRELOAD. The sequence of: CAPTURE-IR \rightarrow EXIT1-IR \rightarrow UPDATE-IR will update the SAMPLE/PRELOAD instruction. For more information refer to the section on instruction definitions.



Instruction Code	Instruction
00000000	EXTEST
1000001	SAMPLE/PRELOAD
10000010	CLAMP
00000011	HIGH-Z
01000001	SAMPLE-IN
01000010	SAMPLE-OUT
00100010	EXTEST-OUT
10101010	IDCODE
1111111	BYPASS
All Others	BYPASS

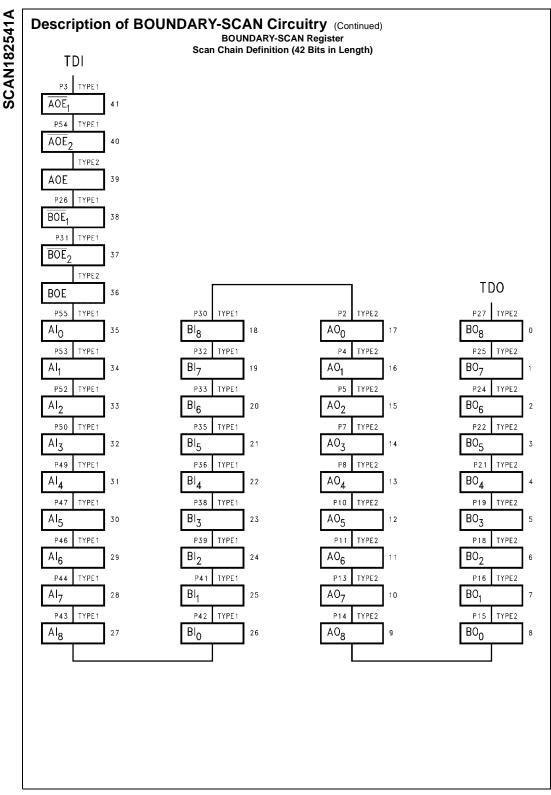




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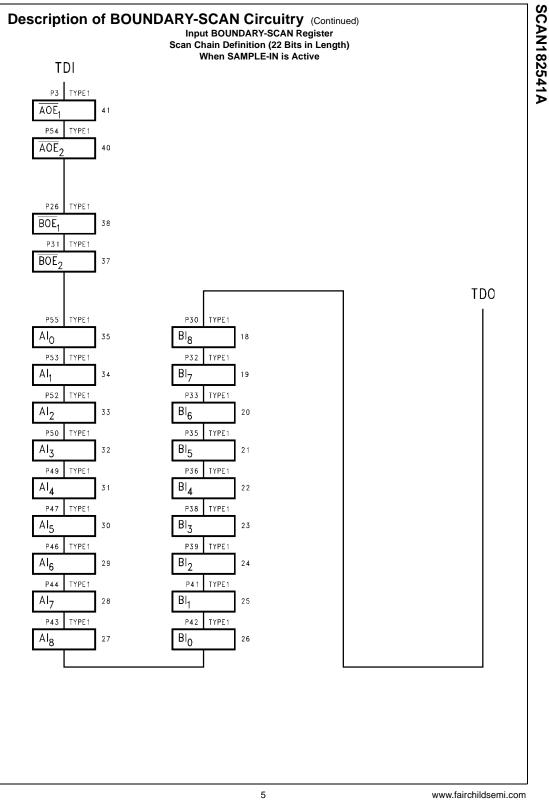
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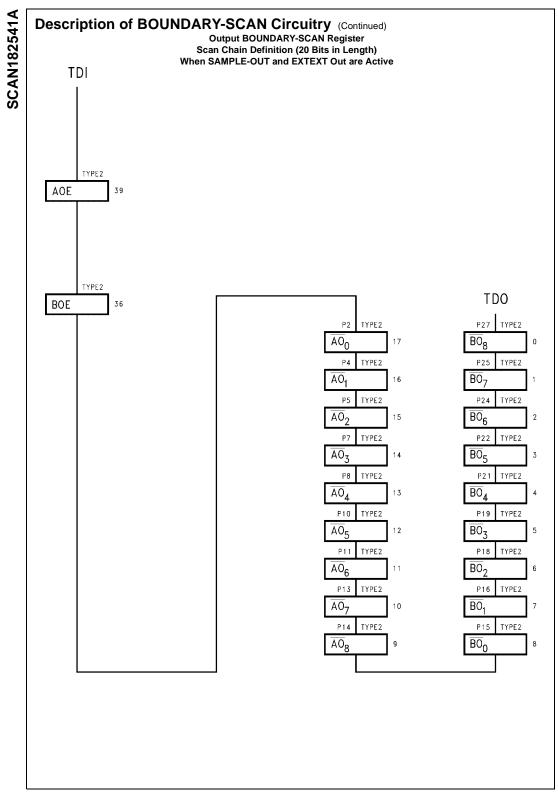
SCAN182541A



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			gister Definition I		
Bit No.	Pin Name	Pin No.	Pin Type	Scan C	ell Type
41	AOE ₁	3	Input	TYPE1	
40	AOE ₂	54	Input	TYPE1	
39	AOE		Internal	TYPE2	Contro
38	BOE ₁	26	Input	TYPE1	Signal
37	BOE ₂	31	Input	TYPE1	
36	BOE		Internal	TYPE2	
35	Al ₀	55	Input	TYPE1	
34	Al ₁	53	Input	TYPE1	
33	Al ₂	52	Input	TYPE1	
32	Al ₃	50	Input	TYPE1	
31	Al ₄	49	Input	TYPE1	A–in
30	AI ₅	47	Input	TYPE1	
29	Al ₆	46	Input	TYPE1	
28	Al ₇	44	Input	TYPE1	
27	Al ₈	43	Input	TYPE1	
26	BI ₀	42	Input	TYPE1	
25	BI ₁	41	Input	TYPE1	
24	Bl ₂	39	Input	TYPE1	
23	Bl ₃	38	Input	TYPE1	
22	Bl ₄	36	Input	TYPE1	B–in
21	BI ₅	35	Input	TYPE1	
20	BI ₆	33	Input	TYPE1	
19	BI ₇	32	Input	TYPE1	
18	BI ₈	30	Input	TYPE1	
17	AO ₀	2	Output	TYPE2	
16	AO ₁	4	Output	TYPE2	
15	AO ₂	5	Output	TYPE2	
14	AO ₃	7	Output	TYPE2	
13	AO ₄	8	Output	TYPE2	A–out
12	AO ₅	10	Output	TYPE2	
11	AO ₆	11	Output	TYPE2	
10	AO ₇	13	Output	TYPE2	
9	AO ₈	14	Output	TYPE2	
8	BO ₀	15	Output	TYPE2	
7	BO ₁	16	Output	TYPE2	
6	BO ₂	18	Output	TYPE2	
5	BO ₃	19	Output	TYPE2	
4	BO ₄	21	Output	TYPE2	B-out
3	BO ₅	22	Output	TYPE2	
2	BO ₆	24	Output	TYPE2	
1	BO ₇	25	Output	TYPE2	
0	BO ₈	27	Output	TYPE2	

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Absolute Maximum Ratings(Note 1)

	-
Storage Temperature	-65°C to +150°C
Ambient Temperature under Bias	-55°C to +125°C
Junction Temperature under Bias	-55°C to +150°C
V_{CC} Pin Potential to Ground Pin	-0.5V to +7.0V
Input Voltage (Note 2)	-0.5V to +7.0V
Input Current (Note 2)	-30 mA to +5.0 mA
Voltage Applied to Any Output	
in Disabled or Power-Off State	-0.5V to +5.5V
in the HIGH State	-0.5V to V _{CC}
Current Applied to Output	
in LOW State (Max)	Twice the Rated I _{OL} (mA)
DC Latchup Source Current	–500 mA
Over Voltage Latchup (I/O)	10V
EDS (HBM) Min.	2000V

Recommended Operating Conditions

Free Air Ambient Temperature	$-40^{\circ}C$ to $+85^{\circ}C$
Supply Voltage	+4.5V to +5.5V
Minimum Input Edge Rate	$(\Delta V / \Delta t)$
Data Input	50 mV/ns
Enable Input	20 mV/ns

Note 1: Absolute Maximum Ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

DC Electrical Characteristics

Symbol	Paramete	er	v _{cc}	Min	Тур	Мах	Units	Conditions
/ _{IH}	Input HIGH Voltage			2.0			V	Recognized HIGH Signal
V _{IL}	Input LOW Voltage					0.8	V	Recognized LOW Signal
V _{CD}	Input Clamp Diode Volta	ge	Min			-1.2	V	I _{IN} = -18 mA
V _{OH}	Output HIGH Voltage		Min	2.5			V	$I_{OH} = -3 \text{ mA}$
			Min	2.0			V	$I_{OH} = -32 \text{ mA}$
V _{OL}	Output LOW Voltage		Min			0.8	V	I _{OL} = 15 mA
Ін	Input HIGH Current	All Others	Max			5	μA	V _{IN} = 2.7V (Note 3)
		All Others	Max			5	μA	$V_{IN} = V_{CC}$
		TMS, TDI	Max			5	μA	$V_{IN} = V_{CC}$
I _{BVI}	Input HIGH Current Breakdown Test		Max			7	μA	V _{IN} = 7.0V
I _{BVIT}	Input HIGH Current Brea	kdown Test (I/O)	Max			100	μA	$V_{IN} = 5.5V$
IIL	Input LOW Current		Max			-5	μA	V _{IN} = 0.5V (Note 3)
		All Others	Max			-5	μA	$V_{IN} = 0.0V$
		TMS, TDI	Max			-385	μA	$V_{IN} = 0.0V$
V _{ID}	Input Leakage Test		0.0	4.75			V	$I_{ID} = 1.9 \ \mu A$
								All Other Pins Grounded
I _{IH} + I _{OZH}	Output Leakage Current		Max			50	μA	$V_{OUT} = 2.7V$
I _{IL} + L _{OZL}	Output Leakage Current		Max			-50	μA	$V_{OUT} = 0.5V$
I _{OZH}	Output Leakage Current		Max			50	μA	V _{OUT} = 2.7V
l _{ozl}	Output Leakage Current		Max			-50	μA	$V_{OUT} = 0.5V$
I _{OS}	Output Short-Circuit Curr	rent	Max	-100		-275	mA	$V_{OUT} = 0.0V$
I _{CEX}	Output HIGH Leakage C	urrent	Max			50	μA	V _{OUT} = V _{CC}
I _{ZZ}	Bus Drainage Test		0.0			100	μA	$V_{OUT} = 5.5V$
								All Others Grounded

Symbol	Param	eter	v _{cc}	Min	Тур	Max	Units	Conditions
I _{CCH}	Power Supply Current		Max			250	μΑ	$V_{OUT} = V_{CC}$; TDI, TMS = V_{CC}
			Max			1.0	mA	$V_{OUT} = V_{CC}$; TDI, TMS = GND
I _{CCL}	Power Supply Current		Max			65	mA	$V_{OUT} = LOW; TDI, TMS = V_{CC}$
			Max			65.8	mA	$V_{OUT} = LOW; TDI, TMS = GND$
I _{CCZ}	Power Supply Current		Max			250	μΑ	TDI, TMS = V_{CC}
			Max			1.0	mA	TDI, TMS = GND
I _{CCT}	Additional I _{CC} /Input	All Other Inputs	Max			2.9	mA	$V_{IN} = V_{CC} - 2.1V$
		TDI, TMS Inputs	Max			3	mA	$V_{IN} = V_{CC} - 2.1V$
ICCD	Dynamic I _{CC}	No Load	Max			0.2	mA/	Outputs Open
							MHz	One Bit Toggling, 50% Duty Cyc

Note 3: Guaranteed not tested.

AC Electrical Characteristics

		V _{cc}	TA	= -40°C to +8	35°C	
Symbol	Parameter	(V)		$C_L = 50 \ pF$		Unit
		(Note 4)	Min	Тур	Max	
t _{PLH}	Propagation Delay	5.0	1.0	3.4	5.2	ns
t _{PHL}	Data to Q		1.9	4.1	6.5	113
t _{PLZ}	Disable Time	5.0	2.0	5.2	8.7	ns
t _{PHZ}			1.9	5.6	9.2	113
t _{PZL}	Enable Time	5.0	2.4	6.1	9.6	ns
t _{PZH}			1.6	5.1	8.5	110
t _{PLH}	Propagation Delay	5.0	3.2	6.0	9.4	ns
t _{PHL}	TCK to TDO		4.5	7.6	11.3	116
t _{PLZ}	Disable Time	5.0	2.5	5.8	9.9	
t _{PHZ}	TCK to TDO		3.7	7.4	11.8	ns
t _{PZL}	Enable Time	5.0	4.9	8.6	12.9	
t _{PZH}	TCK to TDO		3.1	6.7	10.7	ns
t _{PLH}	Propagation Delay		3.7	6.7	10.3	
t _{PHL}	TCK to Data Out during Update-DR State	5.0	4.9	8.3	12.4	n
t _{PLH}	Propagation Delay		4.2	7.9	12.2	
t _{PHL}	TCK to Data Out during Update-IR State	5.0	5.3	9.2	13.8	n
t _{PLH}	Propagation Delay		5.0	9.4	14.6	
t _{PHL}	TCK to Data Out during Test Logic Reset State	5.0	6.2	10.9	16.4	ns
t _{PLZ}	Disable Time		3.7	7.9	13.0	
t _{PHZ}	TCK to Data Out during Update-DR State	5.0	4.3	8.7	13.7	ns
t _{PLZ}	Disable Time		3.7	8.5	14.2	
t _{PHZ}	TCK to Data Out during Update-IR State	5.0	4.3	9.4	14.8	ns
t _{PLZ}	Disable Time		4.7	10.1	16.6	
t _{PHZ}	TCK to Data Out during Test Logic Reset State	5.0	5.5	10.9	17.3	ns
t _{PZL}	Enable Time		5.5	9.8	14.7	
t _{PZH}	TCK to Data Out during Update-DR State	5.0	4.0	7.9	12.5	n
t _{PZL}	Enable Time		5.8	10.9	16.5	
t _{PZH}	TCK to Data Out during Update-IR State	5.0	4.3	9.0	14.4	n
t _{PZL}	Enable Time		6.6	12.5	19.1	
t _{PZH}	TCK to Data Out during Test Logic Reset State	5.0	4.9	10.5	16.9	ns

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		v _{cc}	$T_A = -40^{\circ}C$ to $+85^{\circ}C$	
Symbol	Parameter	(V)	$C_L = 50 \text{ pF}$	Units
		(Note 5)	Guaranteed Minimum	
t _S	Setup Time	5.0	2.2	ns
	Data to TCK (Note 6)	5.0	2.2	ns
t _H	Hold Time	5.0	1.8	ns
	Data to TCK (Note 6)	5.0	1.0	115
t _S	Setup Time, H or L	5.0	3.7	ns
	AOE _n , BOE _n to TCK (Note 7)	5.0	0.1	113
t _H	Hold Time, H or L	5.0	1.8	ns
	TCK to \overline{AOE}_n , \overline{BOE}_n (Note 7)	5.0	1.0	113
t _S	Setup Time, H or L			
	Internal AOE _n , BOE _n ,	5.0	2.7	ns
	to TCK (Note 8)			
t _H	Hold Time, H or L			
	TCK to Internal	5.0	1.8	ns
	AOE _n , BOE _n (Note 8)			
t _S	Setup Time, H or L	5.0	7.5	ns
	TMS to TCK	5.0	1.5	115
t _H	Hold Time, H or L	5.0	1.8	ns
	TCK to TMS	5.0	1.0	115
t _S	Setup Time, H or L	5.0	5.0	20
	TDI to TCK	5.0	0.0	ns
t _H	Hold Time, H or L	5.0	2.0	ns
	TCK to TDI	5.0	2.0	115

 t_{DN}
 Power Down Delay

 Note 5: Voltage Range 5.0V ± 0.5V

Pulse Width TCK

Note 6: This delay represents the timing relationship between the data input and TCK at the associated scan cells numbered 0-8, 9-17, 18-26 and 27-35.

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Note 7: Timing pertains to BSR 38 and 41 or BSR 37 and 40.

Maximum TCK Clock Frequency

Wait Time, Power Up to TCK

Note 8: This delay represents the timing relationship between AOE/BOE and TCK for scan cells 36 and 39 only.

Note: All Input Timing Delays involving TCK are measured from the rising edge of TCK.

Capacitance

t_W

 $\mathbf{f}_{\mathsf{MAX}}$

t_{PU}

Symbol	Parameter	Тур	Units	Conditions, T _A = 25°C
C _{IN}	Input Capacitance	5.8	pF	$V_{CC} = 0.0V$
C _{OUT}	Output Capacitance (Note 9)	13.8	pF	$V_{CC} = 5.0V$

5.0

5.0

5.0

0.0

10.0

10.8

50

100

100

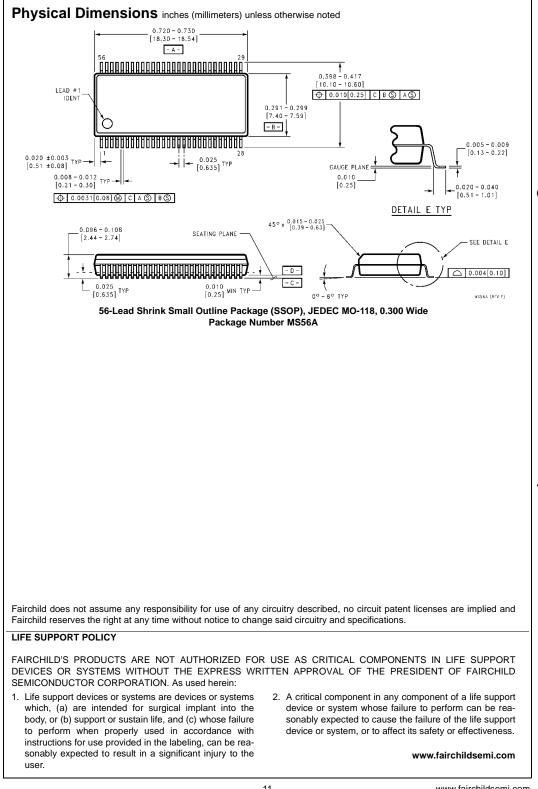
ns

MHz

ns

ms

Note 9: C_{OUT} is measured at frequency f = 1 MHz, per MIL-STD-883B, Method 3012.



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